

### BFQ19S

### Low Noise Silicon Bipolar RF Transistor

- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5 GHz at collector currents from 10 mA to 70 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFQ19S	FG	1 = B	2 = C	3 = E	SOT89

#### **Maximum Ratings** at $T_A$ = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit					
Collector-emitter voltage	V <sub>CEO</sub>	15	V					
Collector-emitter voltage	V <sub>CES</sub>	20						
Collector-base voltage	V <sub>CBO</sub>	20						
Emitter-base voltage	V <sub>EBO</sub>	3						
Collector current	I <sub>C</sub>	120	mA					
Base current	I <sub>B</sub>	12						
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	1	W					
<i>T</i> <sub>S</sub> ≤ 85°C								
Junction temperature	T <sub>J</sub>	150	°C					
Ambient temperature	T <sub>A</sub>	-65 150						
Storage temperature	T <sub>Stg</sub>	-65 150						
Thermal Resistance								

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	65	K/W

 ${}^{1}T_{S}$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup>For the definition of  $R_{\text{thJS}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	15	-	-	V
I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	10	μA
$V_{\rm CE} = 20 \text{ V}, V_{\rm BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	100	μA
$V_{\rm EB} = 2 \text{ V}, I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					

## **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified



Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
AC Characteristics (verified by random sampling	)				
Transition frequency	f <sub>T</sub>	4	5.5	-	GHz
<i>I</i> <sub>C</sub> = 70 mA, <i>V</i> <sub>CE</sub> = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	1.05	1.35	pF
$V_{\rm CB}$ = 10 V, f = 1 MHz, $V_{\rm BE}$ = 0 ,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.4	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	3.9	-	
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,					
collector grounded					
Minimum noise figure	NF <sub>min</sub>				dB
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
<i>f</i> = 900 MHz		-	1.8	-	
<i>f</i> = 1.8 GHz		-	3	-	
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>				
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
<i>f</i> = 900 MHz		-	11.5	-	
<i>f</i> = 1.8 GHz		-	7	-	
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
<i>f</i> = 900 MHz		-	9.5	-	
<i>f</i> = 1.8 GHz		-	4	-	
Third order intercept point at output <sup>2)</sup>	IP <sub>3</sub>	-	32	-	dBm
$V_{CE}$ = 8 V, $I_{C}$ = 70 mA, $Z_{S}$ = $Z_{Sopt}$ , $Z_{L}$ = $Z_{Lopt}$ ,					
<i>f</i> = 1.8 GHz					
1dB Compression point	P <sub>-1dB</sub>	-	22	-	
$V_{CE}$ = 8 V, $I_C$ = 70 mA, $Z_S$ = $Z_{Sopt}$ , $Z_L$ = $Z_{Lopt}$ ,					
f = 1.8 GHz					

## **Electrical Characteristics** at $T_A = 25$ °C, unless otherwise specified

 ${}^{1}\mathrm{G}_{\mathrm{ma}} = |\mathrm{S}_{21}/\mathrm{S}_{12}| \; (\mathrm{k} \cdot (\mathrm{k}^{2} \cdot 1)^{1/2})$ 

<sup>2</sup>IP3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is  $50\Omega$  from 0.2 MHz to 12 GHz



BFQ19S

## Total power dissipation $P_{tot} = f(T_S)$

**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$ 



### Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$ 









### SPICE GP model

For the SPICE model as well as for S-parameters (including noise parameters) please refer to our internet website <u>www.infineon.com/rf.models</u>. Please consult our website and download the latest versions before actually starting your design.









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